

CD4007UB Types

CMOS Dual Complementary Pair Plus Inverter

High-Voltage Types (20-Volt Rating)

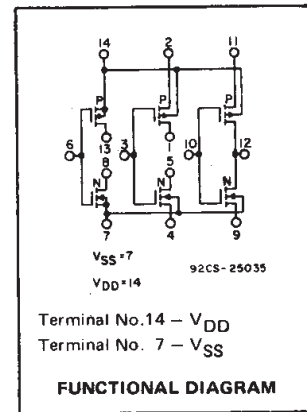
■ CD4007UB types are comprised of three n-channel and three p-channel enhancement-type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in Fig. 2.

More complex functions are possible using multiple packages. Numbers shown in parentheses indicate terminals that are connected together to form the various configurations listed.

The CD4007UB types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- Standardized symmetrical output characteristics
- Medium Speed Operation — t_{PHL} , t_{PLH} = 30 ns (typ.) at 10 V
- 100% tested for quiescent current at 20 V
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"
- Maximum input current of 1 μ A at 18 V over full package-temperature range; 100 nA at 18 V and 25°C



RECOMMENDED OPERATING CONDITIONS

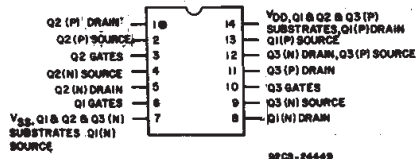
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

Applications:

- Extremely high-input impedance amplifiers
- Shapers
- Inverters
- Threshold detector
- Linear amplifiers
- Crystal oscillators

TERMINAL DIAGRAM
Top View



STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	VO (V)	VIN (V)	VDD (V)					+25			
				-55	-40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, IDD Max.	—	0,5	5	0.25	0.25	7.5	7.5	—	0.01	0.25	μA
	—	0,10	10	0.5	0.5	15	15	—	0.01	0.5	
	—	0,15	15	1	1	30	30	—	0.01	1	
	—	0,20	20	5	5	150	150	—	0.02	5	
Output Low (Sink) Current IOL Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	—	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	—	
Output High (Source) Current, IOH Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	—	
Output Voltage: Low-Level, VOL Max.	—	0,5	5	0.05				—	0	0.05	V
	—	0,10	10	0.05				—	0	0.05	
	—	0,15	15	0.05				—	0	0.05	
Output Voltage: High-Level, VOH Min.	—	0,5	5	4.95				4.95	5	—	V
	—	0,10	10	9.95				9.95	10	—	
	—	0,15	15	14.95				14.95	15	—	
Input Low Voltage, VIL Max.	4.5	—	5	1				—	—	1	V
	9	—	10	2				—	—	2	
	13.5	—	15	2.5				—	—	2.5	
Input High Voltage, VIH Min.	0.5	—	5	4				4	—	—	V
	1	—	10	8				8	—	—	
	1.5	—	15	12.5				12.5	—	—	
Input Current IIN Max.		0,18	18	±0.1	±0.1	±1	±1	—	±10 ⁻⁵	±0.1	μA

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MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD})

Voltages referenced to V_{SS} Terminal) -0.5V to +20V

INPUT VOLTAGE RANGE, ALL INPUTS

..... -0.5V to $V_{DD} + 0.5V$

DC INPUT CURRENT, ANY ONE INPUT

..... $\pm 10mA$

POWER DISSIPATION PER PACKAGE (P_D):

For $T_A = -55^{\circ}C$ to $+100^{\circ}C$ 500mW

For $T_A = +100^{\circ}C$ to $+125^{\circ}C$ Derate Linearly at 12mW/ $^{\circ}C$ to 200mW

DEVICE DISSIPATION PER OUTPUT TRANSISTOR

FOR $T_A = \text{FULL PACKAGE-TEMPERATURE RANGE (All Package Types)}$ 100mW

OPERATING-TEMPERATURE RANGE (T_A)

..... $-55^{\circ}C$ to $+125^{\circ}C$

STORAGE TEMPERATURE RANGE (T_{stg})

..... $-65^{\circ}C$ to $+150^{\circ}C$

LEAD TEMPERATURE (DURING SOLDERING):

At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79mm) from case for 10s max $+265^{\circ}C$

**DYNAMIC ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$; Input $t_r, t_f = 20$ ns,
 $C_L = 50$ pF, $R_L = 200$ K Ω**

CHARACTERISTIC	CONDITIONS	LIMITS			UNITS
		V _{DD} Volts	Typ.	Max.	
Propagation Delay Time: t _{PHL} , t _{PLH}		5	55	110	ns
		10	30	60	
		15	25	50	
Transition Time t _{THL} , t _{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance C _{IN}	Any Input		10	15	pF

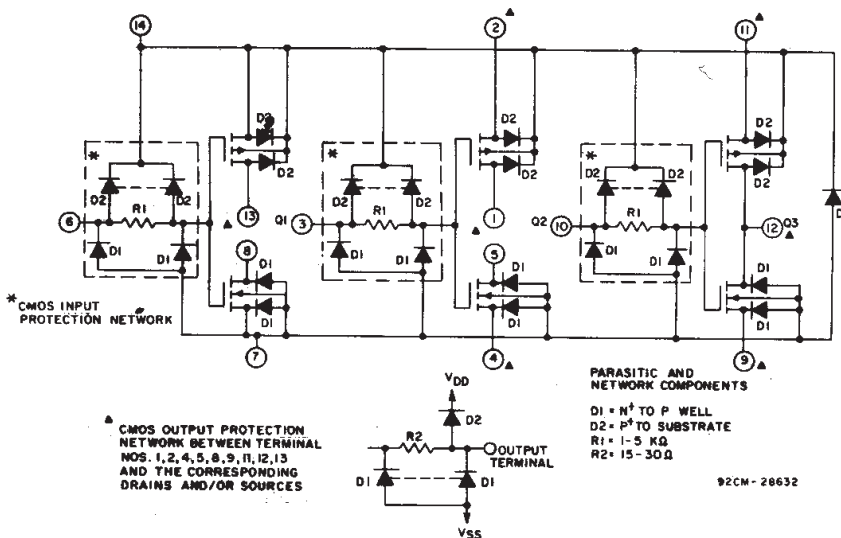
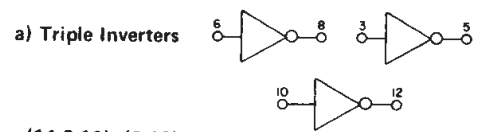


Fig. 1 — Detailed schematic diagram of CD4007UB showing input, output, and parasitic diodes.



(14,2,11); (8,13);
(1,5); (7,4,9)

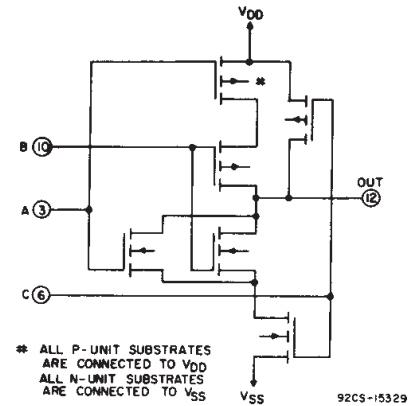


(13,2); (1,11);
(12,5,8); (7,4,9)

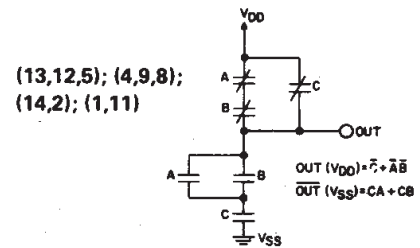


(1,12,13); (2,14,11);
(4,8); (5,9)

d) Tree (Relay) Logic



* ALL P-UNIT SUBSTRATES
ARE CONNECTED TO V_{DD}
ALL N-UNIT SUBSTRATES
ARE CONNECTED TO V_{SS}



(13,12,5); (4,9,8);
(14,2); (1,11)

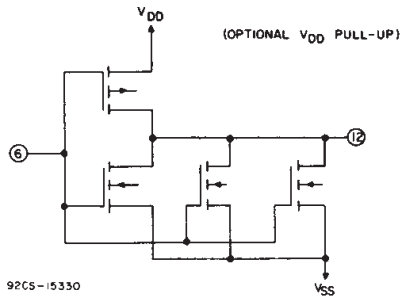
Fig. 2 — Sample CMOS logic circuit arrangements using type CD4007UB.

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COMMERCIAL CMOS
HIGH VOLTAGE ICs

CD4007UB Types

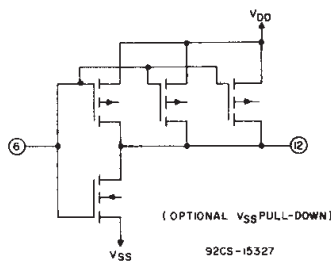
e) High Sink-Current Driver



(6,3,10); (8,5, 12);
(11,14); 7,4,9)



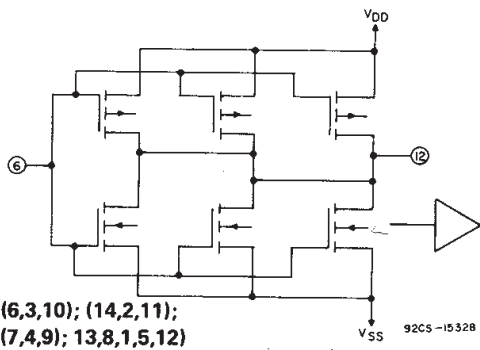
f) High Source-Current Driver



(6,3,10); (13,1,12);
(14,2,11); (7,9)

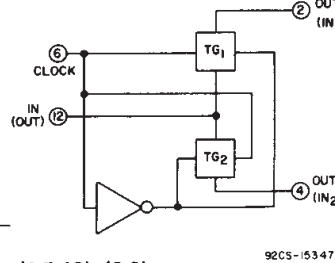


g) High Sink - and Source-Current Driver



(6,3,10); (14,2,11);
(7,4,9); 13,8,1,5,12)

h) Dual Bi-Directional Transmission Gating



(1,5,12); (2,9);
(11,4); (8,13,10);
(6,3)

Fig. 2 - Sample CMOS logic circuit arrangements using type CD4007UB (Cont'd).

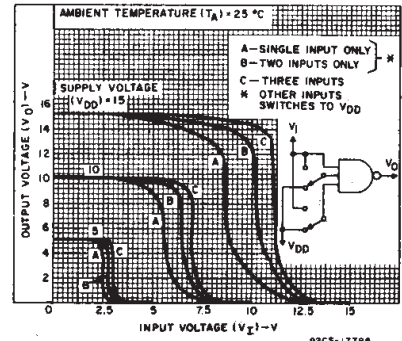


Fig. 3 - Typical voltage-transfer characteristics for NAND gate.

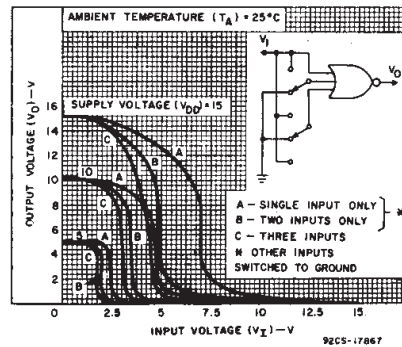


Fig. 4 - Typical voltage-transfer characteristics for NOR gate.

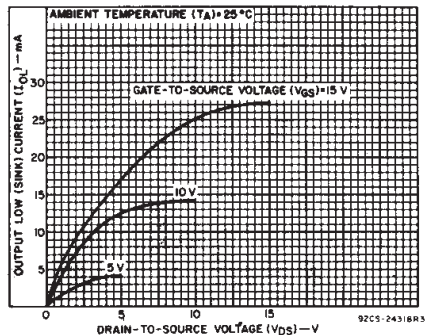


Fig. 5 - Typical output low (sink) current characteristics.

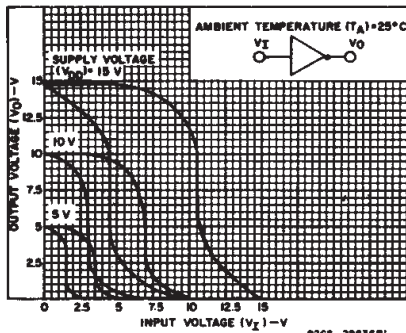


Fig. 6 - Minimum and maximum voltage-transfer characteristics for inverter.

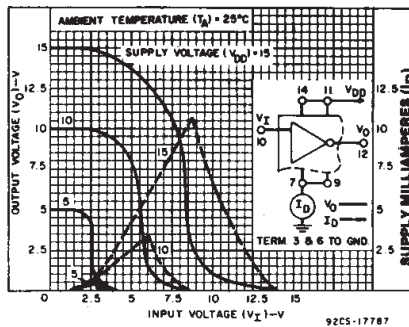


Fig. 7 - Typical current and voltage-transfer characteristics for inverter.

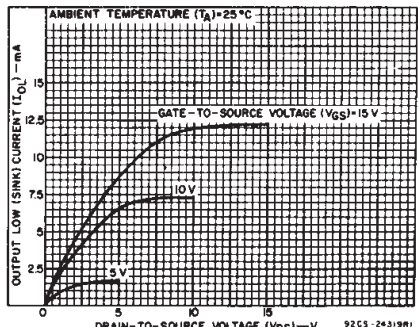


Fig. 8 - Minimum output low (sink) current characteristics.

CD4007UB Types

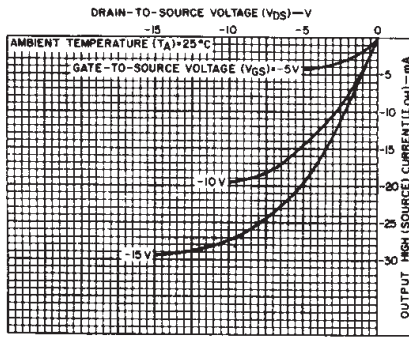


Fig. 9 - Typical output high (source) current characteristics.

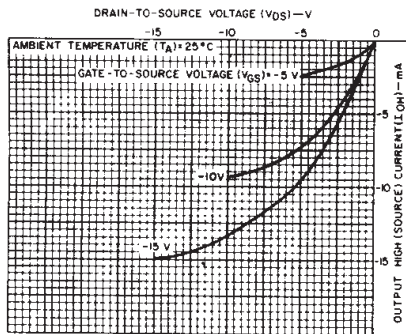


Fig. 10 - Minimum output high (source) current characteristics.

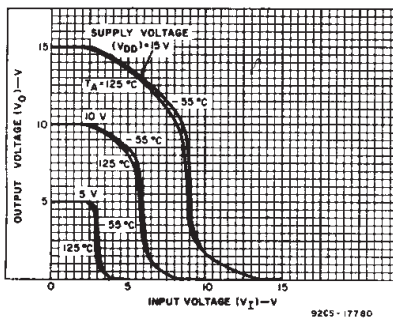


Fig. 11 - Typical voltage-transfer characteristics as a function of temperature.

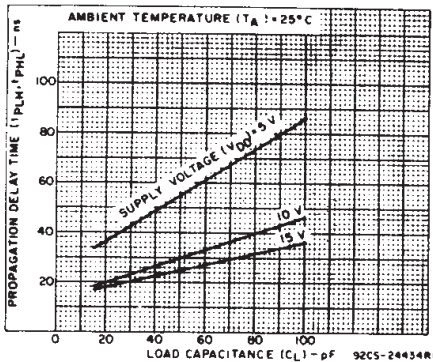


Fig. 12 - Typical propagation delay time vs. load capacitance.

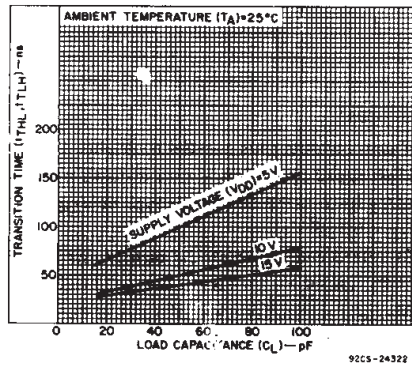


Fig. 13 - Typical transition time vs. load capacitance.

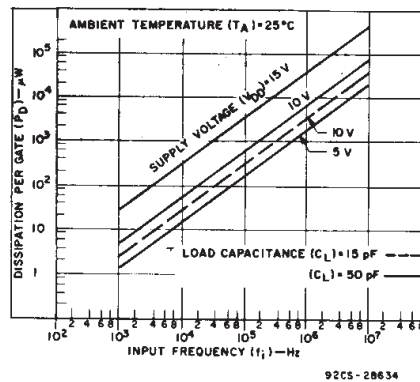


Fig. 14 - Typical dissipation vs. frequency characteristics.

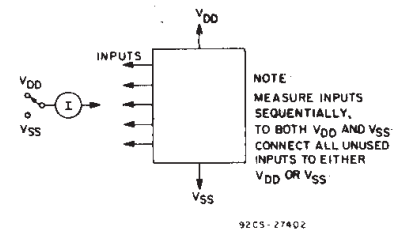


Fig. 15 - Input current test circuit.

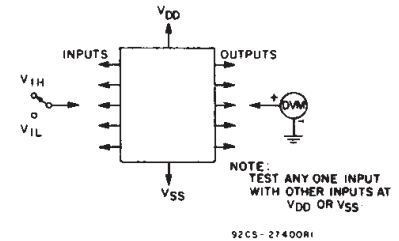


Fig. 16 - Input voltage test circuit.

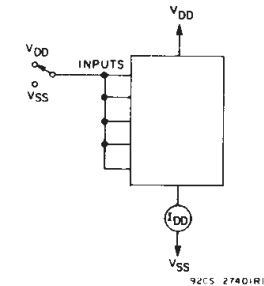
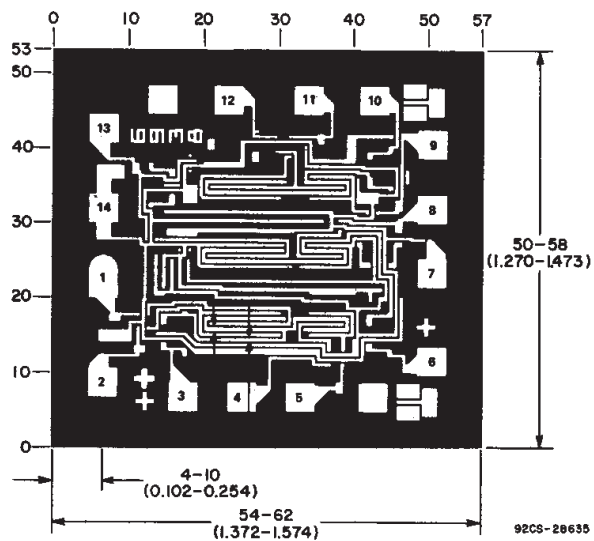


Fig. 17 - Quiescent device current test circuit.



DIMENSIONS AND PAD LAYOUT FOR CD4007UBH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

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